

GENE-8310 A0.3

SubCompact Board With OnBoard Intel ULV Celeron M 1.3GHz CPU

Thermal Image Analysis Report

Report No: 05E080012

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Issue Stamp

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Thermal Image Analysis

SubCompact Board. Intel Celeron(R)-M 1300MHz (100x13.0)

I . Model Name: **GENE-8310 A0.3**

(CPU: On Board CPU Intel Celeron(R) M processor 1300 MHz (100x13.0))
(ha)

II . Description: Intel ULV Celeron-M SubCompact Board With Onboard Intel ULV Celeron M 1.3GHz CPU

III . Date: Mar 18, 2005

IV . Measure Site: AAEON QE Dept.

V . Issued by :Li-Ping Hsieh

VI.Equipment:

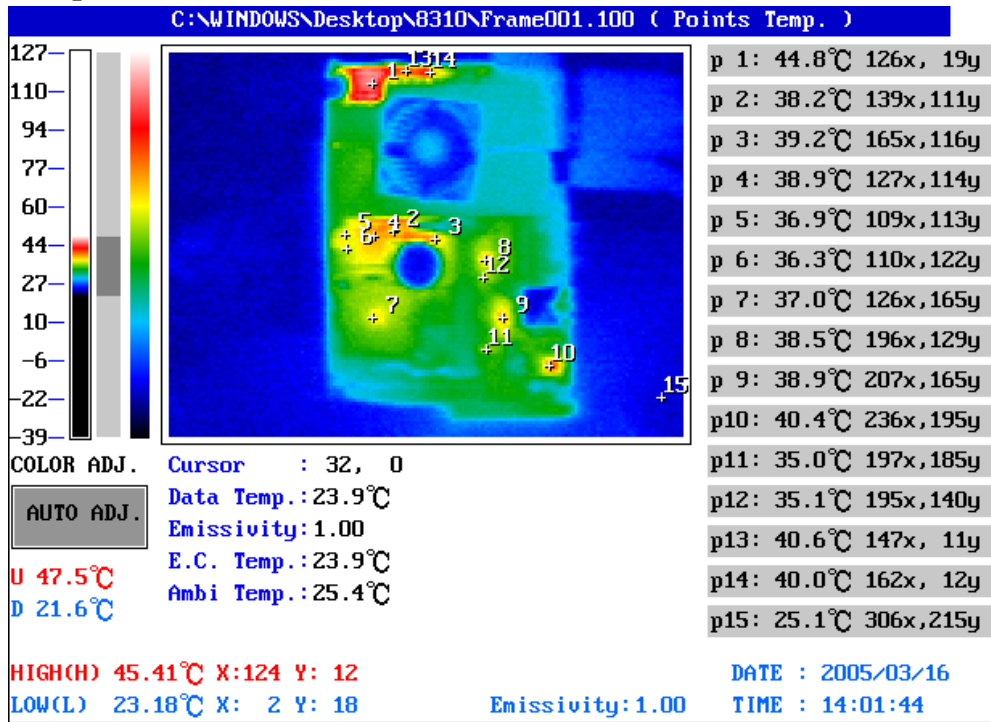
1. TVS-100 series by NIPPON AVIONICS CO., LTD.

VII. Simulation Environment:

- Temperature: Component Side : 25.1 °C
Solder Side : 25.1 °C
- CPU: On Board CPU Intel Celeron(R) M 1300MHz (100x13.0)
- RAM: Hynix /DDR 333 / 512MB
- CF Card: N/A
- Application Software: Run HCT (9.5)System Stress Test under Windows XP Professional+SP1
- Take Picture Time: After Power on 2 hours.

Temperature Profile Test:

Component Side :



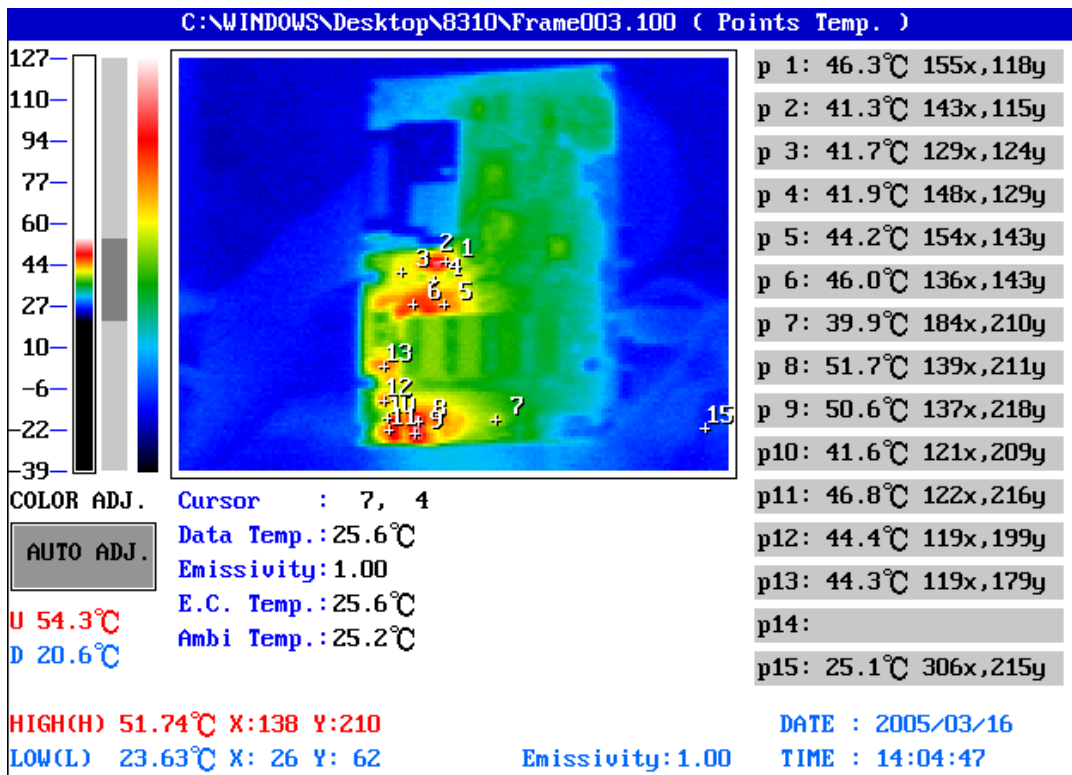
Point	Position	Describe	Tc	Tm (25°C)	Tm (60°C)	Note
1	L2	COIL.0.8uH.SMD.12.5*12.5*5.6mm.DCR=2.5mohm Idc=27.2Amp. 震元.CEP125U-0R8	-60~110°C	44.8°C	79.7	
2	L4	INDUCTOR.3.3uH.20%.SMD DCR=12mohm Isat=27A.VISHAY.IHLP2525CZRZ3R3M01	-25~155	38.2°C	73.1	
3	U6	ICS.IC952601;EE-A040124;14S3260100;TWN	94°C	39.2°C	74.1	
4		IC.SMD.PLCC 32Pin FWH(4MB).SST.49LF004A	-30~115°C	38.9°C	73.8	
5	U1	Dual N-Channel.SMD SO-8.2.5V MOSFET.APEC.AP9926M	-30~125°C	36.9°C	71.8	
6	L1	INDUCTOR.3.3uH 3A.20%.SMD 2Pin.震元.SMTDR54-3R3M	-50~110°C	36.3°C	71.2	
7	U3	IC.SMD.Chipset ICH4.INTEL.FW82801DB SL6DM	0~110°C	37.0°C	71.9	
8	U12	Dual P-Channel MOSFET 2.5V.Vishay.SI9933BDY-T1-E3	125°C	38.5°C	73.4	
9	U13	IC.SMD.SSOP48 Chipset.INTEL.DA82562ET	0~135°C	38.9°C	73.8	
10	U16	IC.SMD LQFP 48Pin.6 Channel AC'97 Audio Codec.REALTEK.ALC655	100°C	40.4°C	75.3	
11	U9	IC.SMD.28Pin QSOP Parallel Term.CMD.Super 1284-04Q	-30~100°C	35.0°C	69.9	
12	U10	IC.SMD SO-8.1.5A.Low Dropout Regulator.Adj(1.2~4.8V).SEMTECH.SC1565IS	-10~115°C	35.1°C	70	
13	L4	INDUCTOR.3.3uH.20%.SMD DCR=12mohm Isat=27A.VISHAY.IHLP2525CZRZ3R3M01	-85~155°C	40.6°C	75.5	
14	R46	CR.(2~10M).(1/16,1/10,1/8,1/4,1/3,3/4,1)W.(+/-1,+/-5%).(0402,0603,0805,1206,1210,2010,2512).SMD;EE-A011069;105	-85~155°C	40.0°C	74.9	
15		Ambient Temperature		25.1°C		

1. Operation Temperature (°C):
 $T_c(\text{Case temp.}) = T_a(\text{Ambient Temp.}) \pm 30^\circ\text{C} = T_j(\text{Junction Temp.}) \pm 25^\circ\text{C}$

Note: The description in red states which temperature is over the specification of the device.

Temperature Profile Test:

Solder Side:



Point	Position	Describe	Tc	Tm (25°C)	Tm (60°C)	Note
1	U30	Dual N-Channel.SMD SO-8.2.5V MOSFET.APEC.AP9926M	-30~125°C	46.3°C	81.2°C	
2	U29	PWR.SMD SO8.N-Channel MOSFET 30V 15A.FAIRCHILD.FDS7760A	-30~125°C	41.3°C	76.2°C	
3	U21	IC.SMD TSSOP-28. DualPower Supply Controller.SEMTECH.SC1485ITSTR	-15~100°C	41.7°C	76.6°C	
4	C198	MLCC.100uF.6.3V.X5R.+20%.1210.SMD	-85~155°C	41.9°C	76.8°C	
5	TC12	SP CAP.220uF.2V.-35~+10%.D(7.3*4.3*1.9mm).9mOhm SMD.Panasonic.EEFSX0D221YR	-70~135°C	44.2°C	79.1°C	
6	TC8	SP CAP.220uF.2V.-35~+10%.D(7.3*4.3*1.9mm).9mOhm SMD.Panasonic.EEFSX0D221YR	-70~135°C	46.0°C	80.9°C	
7	U38	IC.SMD.SO8.Step-Down DC/DC Controller.Anpec.APW7057	-30~100°C	39.9°C	74.8°C	
8	U26	PWR.SMD SO8.N-Channel POWER MOSFET.FAIRCHILD.FDS6680S	-30~125°C	51.7°C	86.6°C	
9	U25	PWR.SMD SO8.N-Channel POWER MOSFET.FAIRCHILD.FDS6680S	-30~125°C	50.6°C	85.5°C	
10	U20	PWR.SMD SO8.N-Channel MOSFET 30V 15A.FAIRCHILD.FDS7760A	-30~125°C	41.6°C	76.5°C	
11	U19	PWR.SMD SO8.N-Channel MOSFET 30V 15A.FAIRCHILD.FDS7760A	-30~125°C	46.8°C	81.7°C	
12	U22	IC.SMD SO8.3A Linear Regulator.Anpec.APL5331KC	125°C	44.4°C	79.3°C	
13	C155	MLCC.100uF.6.3V.X5R.+20%.1210.SMD	-85~155°C	44.3°C	79.2°C	
14						
15		Ambient Temperature		25.1°C		

1. Operation Temperature (°C):
 $T_c(\text{Case temp.}) = T_a(\text{Ambient Temp.}) \pm 30^\circ\text{C} = T_j(\text{Junction Temp.}) \pm 25^\circ\text{C}$

Note: The description in red states which temperature is over the specification of the device.